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CY7C439

Features

- 2048 x 9 FIFO buffer memory
- Bidirectional operation
- · High-speed 28.5-MHz asynchronous reads and writes

YPRESS

- Simple control interface
- Registered and transparent bypass modes
- Flags indicate Empty, Full, and Half Full conditions
- 5V ± 10% supply
- Available in 300-mil DIP, PLCC, LCC, and SOJ packages
- TTL compatible

Functional Description

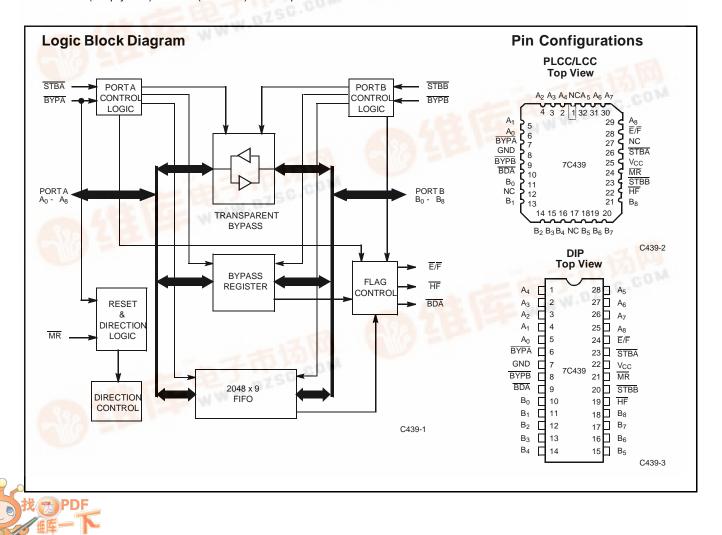
The CY7C439 is a 2048 x 9 FIFO memory capable of bidirectional operation. As the term first-in first-out (FIFO) implies, data becomes available to the output port in the same order that it was presented to the input port. There are two pins that indicate the amount of data contained within the FIFO block— $\overline{E/F}$ (Empty/Full) and \overline{HF} (Half Full). These pins can be

Bidirectional 2K x 9 FIFO

decoded to determine one of four states. Two 9-bit data ports are provided. The direction selected for the FIFO determines the input and output ports. The FIFO direction can be programmed by the user at any time through the use of the reset pin (MR) and the bypass/direction pin (BYPA). There are no control or status registers on the CY7C439, making the part simple to use while meeting the needs of the majority of bidirectional FIFO applications.

FIFO read and write operations may occur simultaneously, and each can occur at up to 28.5 MHz. The port designated as the write port drives its strobe pin (\overline{STBX} , X = A or B) LOW to initiate the write operation. The port designated as the read port drives its strobe pin LOW to initiate the read operation. Output port pins go to a high-impedance state when the associated strobe pin is HIGH. All normal FIFO operations require the bypass control pin (\overline{BYPX} , X = A or B) to remain HIGH.

In addition to the FIFO, two other data paths are provided; registered bypass and transparent bypass. Registered bypass can be considered as a single-word FIFO in the reverse direction to the main FIFO. The





Selection Guide

		7C439-25	7C439-30	7C439-40	7C439-65
Frequency (MHz)		28.5	25	20	12.5
Maximum Access Time (ns)		25	30	40	65
Maximum Operating	Commercial	147	140	130	115
Current (mA)	Military		170	160	145

Functional Description (continued)

bypass register provides a means of sending a 9-bit status or control word to the FIFO-write port. The bypass data available pin (BDA) indicates whether the bypass register is full or empty. The direction of the bypass register is always opposite to that of the main FIFO.

The port designated to write to the bypass register drives its bypass control pin (BYPX) LOW. The other port detects the presence of data by monitoring BDA and reads the data by driving its bypass control pin (BYPX) LOW. Registered bypass operations require that the associated FIFO strobe pin (STBX) remains HIGH. Registered bypass operations do not affect data residing in the FIFO, or FIFO operations at the other port.

Transparent bypass provides a means of transferring a single word (9 bits) of data immediately in either direction. This feature allows the device to act as a simple 9-bit bidirectional buffer. This is useful for allowing the controlling circuitry to access a dumb peripheral for control/programming information.

For transparent bypass, the port wishing to send immediate data to the other side drives both its bypass and its strobe pins LOW simultaneously. This causes the buffered data to be driven out of the other port. On-chip circuitry detects conflicting use of the control pins and causes both data ports to enter a high-impedance state until the conflict is resolved.

Additionally, a Test mode is offered on the CY7C439. This mode allows the user to load data into the FIFO and then read it back out of the same port. Built-In Self Test (BIST) and diagnostic functions can take advantage of these features.

The CY7C439 is fabricated using an advanced 0.8μ N-well CMOS technology. Input ESD protection is greater than 2000V

and latch-up is prevented by reliable layout techniques, guard rings, and a substrate bias generator.

Maximum Ratings

(Above which the useful life may be impaired. For user guide-lines, not tested.) $\label{eq:stable}$

Storage Temperature	–65°C to+150°C
Ambient Temperature with	
Power Applied	–55°C to+125°C
Supply Voltage to Ground Potential	–0.5V to+7.0V
DC Voltage Applied to Outputs	
in High Z State	0.5V to+7.0V
DC Input Voltage	3.0V to +7.0V
Power Dissipation	1.0W
Output Current into Outputs (LOW)	
Static Discharge Voltage	> 2001V
(per MIL-STD-883, Method 3015)	
Latch-Up Current	> 200 mA

Operating Range

Range	Ambient Temperature	v _{cc}
Commercial	0°C to +70°C	5V ± 10%
Military ^[1]	–55°C to +125°C	5V ± 10%

Notes:

1. T_A is the "instant on" case temperature.

Pin Definitions

Signal Name	I/O	Description
A ₍₈₋₀₎	I/O	Data Port Associated with BYPA and STBA
B ₍₈₋₀₎	I/O	Data Port Associated with BYPB and STBB
BYPA	I	Registered Bypass Mode Select for A Side
BYPB	I	Registered Bypass Mode Select for B Side
BDA -	0	Bypass Data Available Flag
STBA	I	Data Strobe for A Side
STBB	I	Data Strobe for B Side
E/F	0	Encoded Empty/Full Flag
ĦF	0	Half Full Flag
MR	I	Master Reset



					39-25	7C43	39-30	7C43	39-40	7C439-65		
Parameter	Description	Test Condit	tions	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Unit
V _{OH}	Output HIGH Voltage	V _{CC} = Min., I _{OH} = -2.0 mA		2.4		2.4		2.4		2.4		V
V _{OL}	Output LOW Voltage	V _{CC} = Min., I _{OL} =	= 8.0 mA		0.4		0.4		0.4		0.4	V
V _{IH}	Input HIGH		Com'l	2.2	V _{CC}	2.2	V _{CC}	2.2	V _{CC}	2.2	V _{CC}	V
	Voltage		Mil			2.2	V _{CC}	2.2	V _{CC}	2.2	V _{CC}	V
V _{IL}	Input LOW Voltage			-3.0	0.8	-3.0	0.8	-3.0	0.8	-3.0	0.8	V
I _{IX}	Input Leakage Current	$GND \le V_I \le V_{CC}$		-10	+10	-10	+10	-10	+10	-10	+10	μA
I _{OZ}	Output Leakage Current	$\overline{\text{STBX}} \ge V_{\text{IH}},$ GND $\le V_{\text{O}} \le V_{\text{CO}}$	2	-10	+10	-10	+10	-10	+10	-10	+10	μA
I _{CC}	Operating Current	V _{CC} = Max.,	Com'l ^[3]		147		140		130		115	mA
		$I_{OUT} = 0 \text{ mA}$	Mil ^[4]				170		160		145	
I _{SB1}	Standby Current	All Inputs =	Com'l		40		40		40		40	mA
		V _{IH} Min.	Mil				45		45		45	
I _{SB2}	Power-Down	All Inputs	Com'l		20		20		20		20	mA
	Current	V _{CC} - 0.2V	Mil				25		25		25	
I _{OS}	Output Short Circuit Current ^[5]	V _{CC} = Max., V _{OUT} = GND			-90		-90		-90		-90	mA

Electrical Characteristics Over the Operating Range^[2]

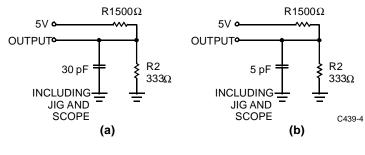
Capacitance^[6]

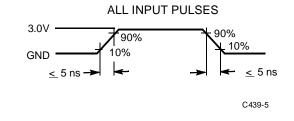
Parameter	Description	Test Conditions	Max.	Unit
C _{IN}	Input Capacitance	$T_A = 25^{\circ}C, f = 1 \text{ MHz},$	8	pF
C _{OUT}	Output Capacitance	$V_{CC} = 4.5V$	10	pF

Notes:



AC Test Loads and Waveform

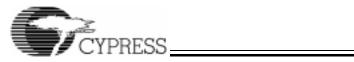




Equivalentto: THÉVENIN EQUIVALENT 200Ω OUTPUT • • 2V

Switching Characteristics Over the Operating Range^[2,7]

		7C4	39-25	7C4	39-30	7C4	7C439-40		7C439-65	
Parameter	Description	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Unit
t _{RC}	Read Cycle Time	35		40		50		80		ns
t _A	Access Time		25		30		40		65	ns
t _{RR}	Read Recovery Time	10		10		10		15		ns
t _{PR}	Read Pulse Width	25		30		40		65		ns
t _{LZR} ^[8, 9]	Read LOW to Low Z	3		3		3		3		ns
t _{DVR} ^[8, 9]	Data Valid from Read HIGH	3		3		3		3		ns
t _{HZR} ^[8, 9]	Read HIGH to High Z		18		20		25		30	ns
t _{WC}	Write Cycle Time	35		40		50		80		ns
t _{PW}	Write Pulse Width	25		30		40		65		ns
t _{HWZ} ^[8, 9]	Write HIGH to Low Z	10		10		10		10		ns
t _{WR}	Write Recovery Time	10		10		10		15		ns
t _{SD}	Data Set-Up Time	15		18		20		30		ns
t _{HD}	Data Hold Time	0		0		0		10		ns
t _{MRSC}	MR Cycle Time	35		40		50		80		ns
t _{PMR}	MR Pulse Width	25		30		40		65		ns
t _{RMR}	MR Recovery Time	10		10		10		15		ns
t _{RPS}	STBX HIGH to MR HIGH	25		30		40		65		ns
t _{RPBS}	BYPA to MR HIGH	10		10		15		20		ns
t _{RPBH}	BYPA Hold after MR HIGH	0		0		0		0		ns
t _{BDH}	MR LOW to BDA HIGH		35		40		50		80	ns
t _{BSR}	STBX HIGH to BYPA LOW	10		10		10		15		ns
t _{EFL}	MR to E/F LOW		35		40		50		80	ns
t _{HFH}	MR to HF HIGH		35		40		50		80	ns
t _{BRS}	BYPX HIGH to STBX LOW	10		10		10		15		ns
t _{REF}	STBX LOW to E/F LOW (Read)		25		30		35		60	ns
t _{RFF}	STBX HIGH to E/F HIGH (Read)		25		30		35		60	ns
t _{WEF}	STBX HIGH to E/F HIGH (Write)		25		30		35		60	ns



		7C43	39-25	7C43	7C439-30		39-40	7C439-65		
Parameter	Description	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Unit
t _{WFF}	STBX LOW to E/F LOW (Write)		25		30		35		60	ns
t _{BDA}	BYPX HIGH to BDA LOW (Write)		25		30		35		60	ns
t _{BDB}	BYPX HIGH to BDA HIGH (Read)		25		30		35		60	ns
t _{BA}	BYPX LOW to Data Valid (Read)		30		30		40		60	ns
t _{BHZ} ^[8, 9]	BYPX HIGH to High Z (Read)		18		20		25		30	ns
t _{TSB}	STBX HIGH to BYPX LOW Set-Up	10		10		10		15		ns
t _{TBS}	STBX LOW after BYPX LOW	0	10	0	10	0	10	0	10	ns
t _{TSN}	STBX HIGH Recovery Time	10		10		10		15		ns
t _{TSD} ^[8, 9]	STBX HIGH to Data High Z		18		20		25		30	ns
t _{TBN}	BYPX HIGH Recovery Time	10		10		10		15		ns
t _{TBD}	BYPX HIGH to Data High Z		18		20		25		30	ns
t _{TPD} ^[8, 9]	STBX LOW to Data Valid		20		20		30		55	ns
t _{DL}	Transparent Propagation Delay		20		20		25		30	ns
t _{ESD} [^{8, 9]}	STBX LOW to High Z		18		20		25		30	ns
t _{EBD} ^[8, 9]	BYPX LOW to High Z		18		20		25		30	ns
t _{EDS}	STBX HIGH to Low Z		18		20		25		30	ns
t _{EDB}	BYPX HIGH to Low Z		18		20		25		30	ns
t _{BPW}	BYPX Pulse Width (Trans.)	25		30		40		65		ns
t _{TSP}	STBX Pulse Width (Trans.)	20		20		30		55		ns
t _{BLZ} [8, 9]	BYPX LOW to Low Z (Read)	10		10		10		10		ns
t _{BDV}	BYPX HIGH to Data Invalid (Read)	3		3		3		3		ns
t _{WHF}	STBX LOW to HF LOW (Write)		35		40		50		80	ns
t _{RHF}	STBX HIGH to HF HIGH (Read)		35		40		50		80	ns
t _{RAE}	Effective Read from Write HIGH		25		30		35		60	ns
t _{RPE}	Effective Read Pulse Width after E/F HIGH	25		30		40		65		ns
t _{WAF}	Effective Write from Read HIGH		25		30		35		60	ns
t _{WPF}	Effective Write Pulse Width after $\overline{E}/\overline{F}$ HIGH	25		30		40		65		ns
t _{BSU}	Bypass Data Set-Up Time	15		18		20		30		ns
t _{BHL}	Bypass Data Hold Time	0		0		0		10		ns

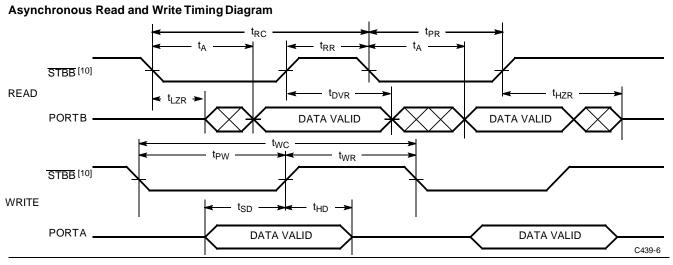
Switching Characteristics Over the Operating Range^[2, 7] (Continued)

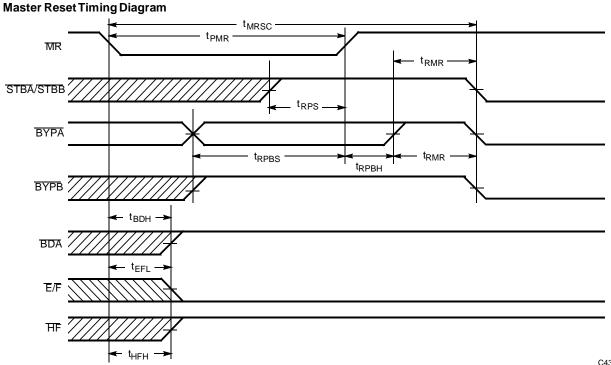
Notes:

Test conditions assume signal transition time of 5 ns or less, timing reference levels of 1.5V, and output loading of the specified I_{OL}/I_{OH} and 30-pF load capacitance as in part (a) of AC Test Loads, unless otherwise specified.
 t_{DVR}, t_{BDV}, t_{HZR}, t_{TBD}, t_{BHZ}, t_{EBD}, t_{ESD}, t_{ESD}, t_{TSD}, t_{LZR}, t_{HWZ}, and t_{BLZ} use capacitance loading as in part (b) of AC Test Loads.
 t_{HZR}, t_{TBD}, t_{BHZ}, t_{EBD}, t_{ESD}, t_{ESD}, t_{TSD}, t_{LZR}, t_{HWZ}, and t_{BLZ} use capacitance loading as in part (b) of AC Test Loads.
 t_{HZR}, t_{TBD}, t_{BHZ}, t_{EBD}, t_{ESD}, and t_{TSD} transition is measured at +500 mV from V_{OL} and - 500 mV from V_{OH}, t_{DVR} and t_{BDV} transition is measured at the 1.5V level. t_{LZR}, t_{HWZ}, and t_{BLZ} transition is measured at ±100 mV from the steady state.



Switching Waveforms



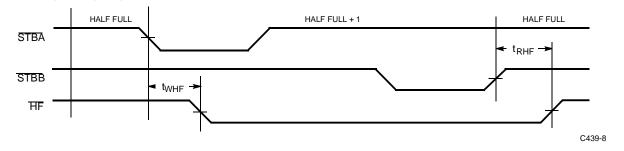


C439-7

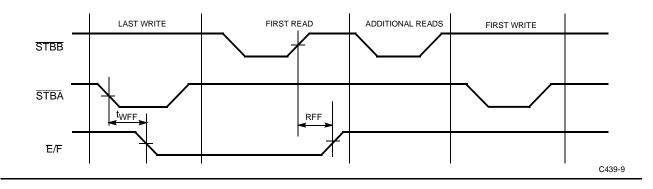


Switching Waveforms (Continued)

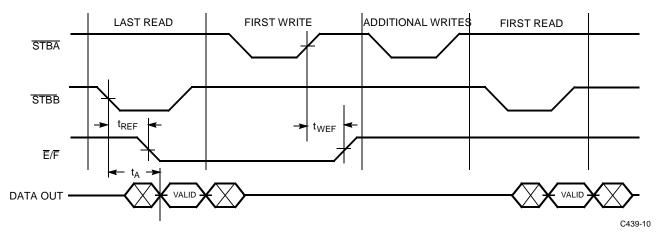
Half–Full FlagTimingDiagram^[11]



Last Write to First Read Empty/FullFlagTimingDiagram^[11]



Last Read to First Write Empty/Full Flag Timing Diagram^[11]



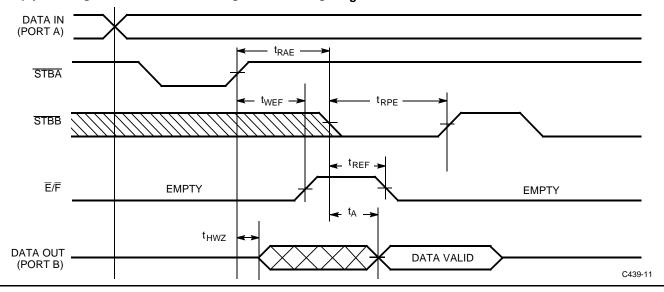
Notes:

- Direction selected Port A to Port B.
 Direction selected as A to B.

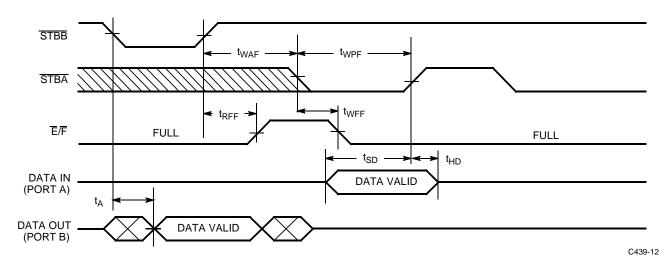


Switching Waveforms (Continued)

Empty/Full Flag and Read Bubble–Through Mode Timing Diagram^[11]



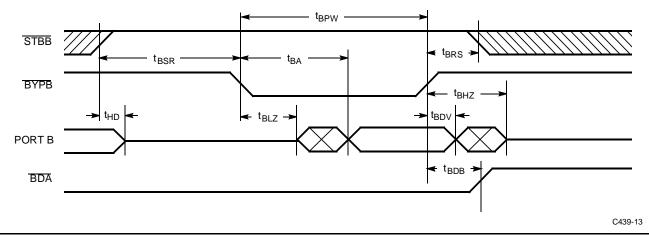
Empty/Full Flag and Write Bubble–Through Mode Timing Diagram^[11]



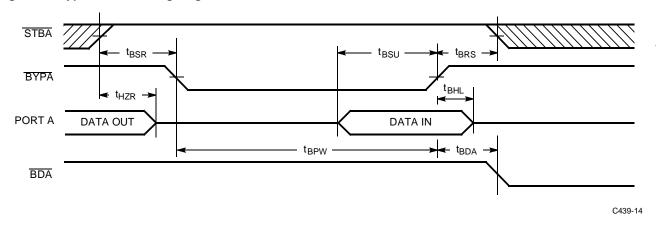


Switching Waveforms (Continued)

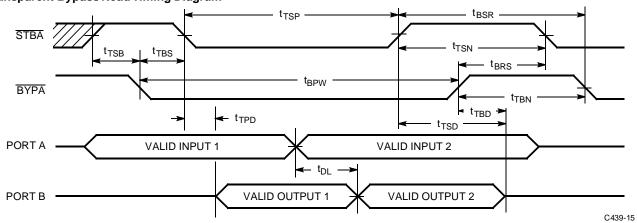
Registered Bypass Read Timing Diagram^[12]



Registered Bypass Write Timing Diagram^[13]



Transparent Bypass Read Timing Diagram^[14]



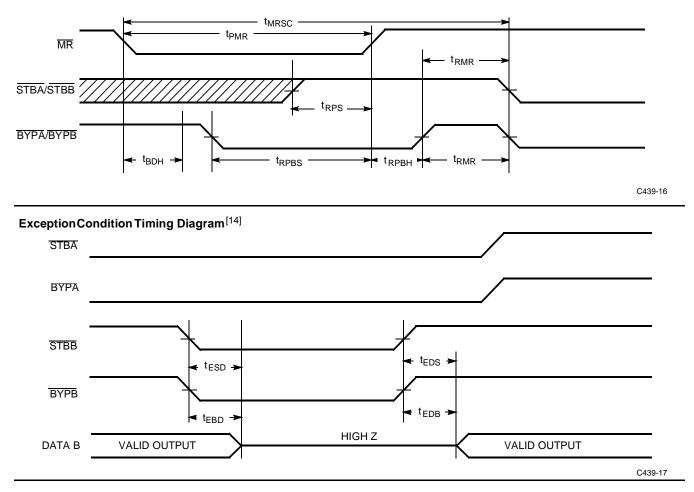
Notes:

- Port B selected to read bypass register (FIFO direction Port B to Port A). Port A selected to write bypass register (FIFO direction Port B to Port A. Diagram shows transparent bypass initiated by Port A. Times are identical if initiated by Port B. 12. 13. 14.



Switching Waveforms (Continued)

Test Mode Timing Diagram



Architecture

The CY7C439 consists of a 2048 by 9-bit dual-ported RAM array, a read pointer, a write pointer, data switching circuitry, buffers, a bypass register, control signals (\overline{STBA} , \overline{STBB} , \overline{BYPA} , \overline{BYPB} , \overline{MR}), and flags ($\overline{E/F}$, \overline{HF} , \overline{BDA}).

Operation at Power-On

Upon power-up, the FIFO must be reset with a Master Reset (MR) cycle. During an MR cycle, the user can initialize the device by choosing the direction of FIFO operation (see *Table 1*). There is a minimum LOW period for MR, but no maximum time. The state of BYPA is latched internally by the rising edge of MR and used to determine the direction of subsequent data operations.

Resetting the FIFO

During the reset condition (see *Table 1*), the FIFO three-states the data ports, sets \overline{BDA} and \overline{HF} HIGH, $\overline{E/F}$ LOW, and ignores the state of $\overline{BYPA/B}$ and $\overline{STBA/B}$. The bypass registers are initialized to zero. During this time the user is expected to set the direction of the FIFO by driving \overline{BYPA} HIGH or LOW, and \overline{BYPB} , \overline{STBA} , and \overline{STBB} HIGH. If \overline{BYPA} is LOW (selecting direction B>A), the FIFO will then remain in a reset condition until the user terminates the reset operation by driving $\overline{\text{BYPA}}$ HIGH. If $\overline{\text{BYPA}}$ is HIGH (selecting direction A>B), the reset condition terminates after the rising edge of $\overline{\text{MR}}$. The entire reset phase can be accomplished in one cycle time of tRC.

FIFO Operation

The operation of the FIFO requires only one control pin per port (STBX). The user determines the direction of the FIFO data flow by initiating an MR cycle (see Table 1), which clears the FIFO and bypass register and sets the data path and control signal multiplexers. The bypass register is configured in the opposite direction to the FIFO data flow. The FIFO direction can be reversed at any time by initiating another MR cycle. Data is written into the FIFO on the rising edge of the input, STBX, and read from the FIFO by a low level at the output, STBX. The two ports are asynchronous and independent. If the user attempts to read the FIFO when it is empty, no action takes place (the read pointer is not incremented) until the other port writes to the FIFO. Then a bubble-through read takes place, in which the read strobe is generated internally and the data becomes available at the read port shortly thereafter if the read strobe (STBX) is still LOW. Similarly, for an attempted write operation when the FIFO is full, no internal operation takes place until the other port performs a read operation, at



which time the bubble-through write is performed if the write strobe $\overline{(\text{STBX})}$ is still LOW.

Registered Bypass Operation

The registered bypass feature provides a means of transferring one 9-bit word of data in the opposite direction to normal data flow without affecting either the FIFO contents or the FIFO write operations at the other port. The bypass register is configured during reset to provide a data path in the opposite direction to that of the FIFO (see *Table 1*). For example, if port A is writing data to the FIFO (hence port B is reading data from the FIFO) then BYPB is used to write to the bypass register at port B, and BYPA is used to read a single word from the bypass register at port A. The bypass data available flag (BDA) is generated to notify port A that bypass data is available. BDA goes true on the trailing edge of the BYPX write operation and false upon the trailing edge of the BYPX read operation.

Data is written on the rising edge of BYPX into the bypass register for later retrieval by the other port, regardless of the state of BDA. The bypass register is read by a low level at BYPX, regardless of the state of BDA.

Transparent Bypass Operation

The transparent bypass feature provides a means of sending immediate data "around" the FIFO in either direction. The FIFO contents are not affected by the use of transparent bypass, but the control signals for transparent bypass are shared with those of the normal FIFO operation. Hence there are limitations on the use of transparent bypass to ensure that data integrity and ease of use are preserved. The port wishing to send immediate data must ensure that the other port will not attempt a FIFO read or write during the transparent bypass cycle. If this is not possible, registered bypass or external circuitry should be used. Transparent bypass mode is initiated by bringing both BYPA and STBA LOW together. Care should be taken to observe the following constraints on the timing relationships. Since STBA is used for normal FIFO operations, it must follow BYPA falling edge by tTBS to prevent erroneous FIFO read or write operations. Since BYPA is used alone to initiate registered bypass read and write, it is internally delayed before initiating registered bypass. If STBA falls during this time, delay registered bypass is averted, and transparent bypass is initiated. Identical arguments apply to BYPB and STBB.

If a transparent bypass sequence is successfully accomplished, data presented to the initiating port (port A in the above discussion) will be buffered to the other (port B) after tDL. Either port can initiate a transparent bypass operation at any time, but if the control signals (STBA/B, BYPA/B) are in conflict (exception condition), internal circuitry will switch both ports to high-impedance until the conflict is resolved.

Test Mode Operation

The Test mode feature provides a means of reading the FIFO contents from the same port that the data was written to the FIFO. This feature is useful for Built-In Self Test (BIST) and diagnostic functions. To utilize this capability, initialize FIFO direction A to B and load data into the FIFO using normal write timing. In order to read data back out of the same port (port A), initiate a MR cycle with both BYPA and BYPB LOW (see Test Mode Timing diagram). After completing the cycle, the data can be read out of port A in FIFO order. Data will be inverted when read out of the device. Also, flags are not valid when reading data.

Flag Operation

There are two flags, Empty/Full ($\overline{E}/\overline{F}$) and Half Full (\overline{HF}), which are used to decode four FIFO states (see *Table 4*). The states are empty, 1-1024 locations full, 1025-2047 locations full, and full. Note that two conditions cause the $\overline{E}/\overline{F}$ pin to go LOW, Empty and Full, hence both flag pins must be used to resolve the two conditions.

MR	BYPA	BYPB	STBA	STBB	Action
1	Х	Х	Х	Х	Normal Operation
Г	1	1	1	1	FIFO Direction A to B, Registered Bypass Direction B to A
	0	1	1	1	FIFO Direction B to A, Registered Bypass Direction A to B
0	Х	Х	Х	Х	Reset Condition

Table 1. FIFO Direction Select Truth

Table 2. Bypass Operation Truth Table

Direction	STBA	BYPA	STBB	BYPB	Action
ΑÁΒ	Ъ	1	Ъ	1	Normal FIFO Operations, Write at A, Read at B
АÁВ	1	Т	Ъ	1	Normal FIFO Read at B, Bypass Register Read at A
АÁВ	U	1	1	Ъ	Normal FIFO Write at A, Bypass Register Write at B



Table 2. Bypass Operation Truth Table

ВÁА	U	1	U	1	Normal FIFO Operations, Write at B, Read at A
BÁA	1	T	T	1	Normal FIFO Write at B, Bypass Register Write at A
ВÁА	T	1	1	Т	Normal FIFO Read at A, Bypass Register Read at B
Х	0	0	1	1	No FIFO Operations, Transparent Data A to B
Х	1	1	0	0	No FIFO Operations, Transparent Data B to A

Table 3. Exception Conditions: Operation Not Defined

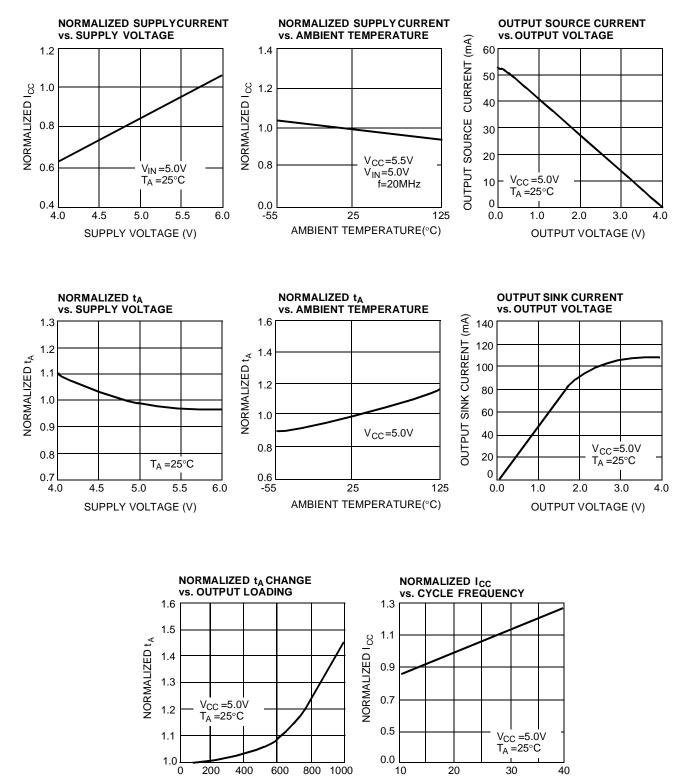
Direction	STBA	BYPA	STBB	BYBP	Action
Х	0	1	0	0	Data Buses High Impedance
Х	1	0	0	0	Data Buses High Impedance
Х	0	0	0	0	Data Buses High Impedance
Х	0	0	1	0	Data Buses High Impedance
Х	0	0	0	1	Data Buses High Impedance

Table 4. Flag Truth Table.

Ē/Ē	HF	State
0	1	Empty
1	1	1-1024 Locations Full
1	0	1025-2047 Locations Full
0	0	Full

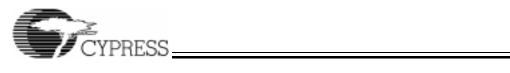


Typical DC and AC Characteristics



CYCLE FREQUENCY (MHz)

CAPACITANCE (pF)



Ordering Information

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
25	CY7C439-25JC	J65	32-Lead Plastic Leaded Chip Carrier	Commercial
	CY7C439-25PC	P21	28-Lead (300-Mil) Molded DIP	
30	CY7C439-30JC	J65	32-Lead Plastic Leaded Chip Carrier	Commercial
	CY7C439-30PC	P21	28-Lead (300-Mil) Molded DIP	
	CY7C439-30DMB	D22	28-Lead (300-Mil) CerDIP	Military
	CY7C439-30LMB	L55	32-Pin Rectangular Leadless Chip Carrier	
40	CY7C439-40JC	J65	32-Lead Plastic Leaded Chip Carrier	Commercial
	CY7C439-40PC	P21	28-Lead (300-Mil) Molded DIP	
	CY7C439-40DMB	D22	28-Lead (300-Mil) CerDIP	Military
	CY7C439-40LMB	L55	32-Pin Rectangular Leadless Chip Carrier	
6.5	CY7C439-65JC	J65	32-Lead Plastic Leaded Chip Carrier	Commercial
	CY7C439-65PC	P21	28-Lead (300-Mil) Molded DIP	
	CY7C439-65DMB	D22	28-Lead (300-Mil) CerDIP	Military
	CY7C439-65LMB	L55	32-Pin Rectangular Leadless Chip Carrier	



MILITARY SPECIFICATIONS Group A Subgroup Testing

DC Characteristics

Parameters	Subgroups
V _{OH}	1, 2, 3
V _{OL}	1, 2, 3
V _{IH}	1, 2, 3
V _{IL} Max.	1, 2, 3
I _{IX}	1, 2, 3
I _{CC}	1, 2, 3
I _{SB1}	1, 2, 3
I _{SB2}	1, 2, 3
I _{OS}	1, 2, 3
I _{OZ}	1, 2, 3

Switching Characteristics

Parameters	Subgroups
t _{RC}	9, 10, 11
t _A	9, 10, 11
t _{RR}	9, 10, 11
t _{PR}	9, 10, 11
t _{LZR}	9, 10, 11
t _{DVR}	9, 10, 11
t _{HZR}	9, 10, 11
t _{WC}	9, 10, 11
t _{PW}	9, 10, 11
t _{HWZ}	9, 10, 11
t _{WR}	9, 10, 11
t _{SD}	9, 10, 11
t _{HD}	9, 10, 11
t _{MRSC}	9, 10, 11
t _{PMR}	9, 10, 11
t _{RMR}	9, 10, 11
t _{RPS}	9, 10, 11
t _{RPBS}	9, 10, 11
t _{RPBH}	9, 10, 11
t _{BDH}	9, 10, 11
t _{BSR}	9, 10, 11

Switching Characteristics

Parameters	Subgroups
t _{EFL}	9, 10, 11
t _{HFH}	9, 10, 11
t _{BRS}	9, 10, 11
t _{REF}	9, 10, 11
t _{RFF}	9, 10, 11
t _{WEF}	9, 10, 11
t _{WFF}	9, 10, 11
t _{WHF}	9, 10, 11
t _{RHF}	9, 10, 11
t _{RAE}	9, 10, 11
t _{RPE}	9, 10, 11
t _{WAF}	9, 10, 11
t _{WPF}	9, 10, 11
t _{BSU}	9, 10, 11
t _{BHL}	9, 10, 11
t _{BDA}	9, 10, 11
t _{BDB}	9, 10, 11
t _{BA}	9, 10, 11
t _{BHZ}	9, 10, 11
t _{TSB}	9, 10, 11
t _{TBS}	9, 10, 11
t _{TSN}	9, 10, 11
t _{TSD}	9, 10, 11
t _{TBN}	9, 10, 11
t _{TBD}	9, 10, 11
t _{TPD}	9, 10, 11
t _{DL}	9, 10, 11
t _{ESD}	9, 10, 11
t _{EBD}	9, 10, 11
t _{EDS}	9, 10, 11
t _{EDB}	9, 10, 11
t _{BPW}	9, 10, 11
t _{TSP}	9, 10, 11
t _{BLZ}	9, 10, 11
t _{BDV}	9, 10, 11

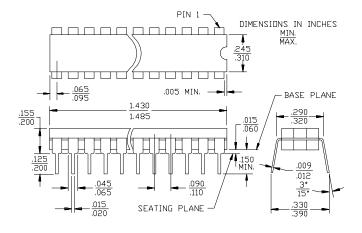
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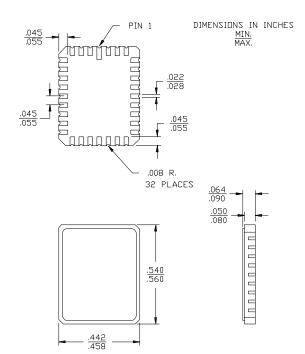


Package Diagrams

28-Lead (300-Mil) CerDIP D22

MIL-STD-1835 D-15Config.A

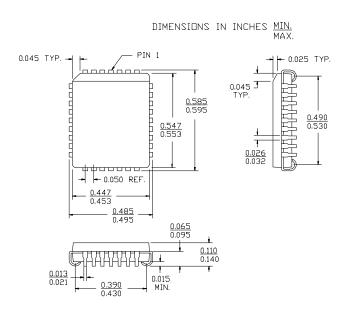




32–Pin Rectangular Leadless Chip Carrier L55

MIL-STD-1835 C-12

32–Lead Plastic Leaded Chip Carrier J65





Package Diagrams (Continued)

28-Lead (300-Mil) Molded DIP P21

